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BSS123

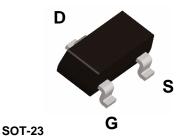
N-Channel Logic Level Enhancement Mode Field Effect Transistor

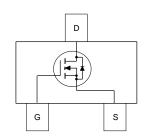
General Description

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- 0.17 A, 100 V. $R_{DS(ON)} = 6\Omega$ @ $V_{GS} = 10$ V $R_{DS(ON)} = 10\Omega$ @ $V_{GS} = 4.5$ V
- High density cell design for extremely low R_{DS(ON)}
- Rugged and Reliable
- Compact industry standard SOT-23 surface mount package





Absolute Maximum Ratings T_A=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|-----------------------------------|--|----------|-------------|-------|
| V _{DSS} | Drain-Source Voltage | | 100 | V |
| V _{GSS} | Gate-Source Voltage | | ±20 | V |
| I _D | Drain Current - Continuous | (Note 1) | 0.17 | А |
| | – Pulsed | | 0.68 | |
| P _D | Maximum Power Dissipation | (Note 1) | 0.36 | W |
| | Derate Above 25°C | | 2.8 | mW/°C |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | | -55 to +150 | °C |
| T _L | Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds | | 300 | |

Thermal Characteristics

| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1) | 350 | °C/W |
|-----------------|---|----------|-----|------|
|-----------------|---|----------|-----|------|

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|--------|-----------|------------|------------|
| SA | BSS123 | 7" | 8mm | 3000 units |

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|--|---|--|------|-------------------|---------------|-------|
| Off Char | acteristics | | | · | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$ | 100 | | | V |
| $\Delta BV_{DSS} \over \Delta T_{J}$ | Breakdown Voltage Temperature Coefficient | I_D = 250 μ A,Referenced to 25°C | | 97 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | μΑ |
| | | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V T}_{J} = 125^{\circ}\text{C}$ | | | 60 | μΑ |
| | | $V_{DS} = 20 \text{ V}, \qquad V_{GS} = 0 \text{ V}$ | | | 10 | nA |
| I _{GSS} | Gate-Body Leakage. | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | ±50 | nA |
| On Chara | acteristics (Note 2) | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$ | 0.8 | 1.7 | 2 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | I _D = 1 mA,Referenced to 25°C | | -2.7 | | mV/°C |
| $R_{\text{DS(on)}}$ | Static Drain–Source On–Resistance | $ \begin{vmatrix} V_{GS} = 10 \text{ V}, & I_D = 0.17 \text{ A} \\ V_{GS} = 4.5 \text{ V}, & I_D = 0.17 \text{ A} \\ V_{GS} = 10 \text{ V}, I_D = 0.17 \text{ A}, T_J = 125^{\circ}\text{C} \\ \end{vmatrix} $ | | 1.2 1.3 2.2 | 6 10 12 | Ω |
| I _{D(on)} | On-State Drain Current | $V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$ | 0.68 | | | Α |
| g _{FS} | Forward Transconductance | $V_{DS} = 10V$, $I_{D} = 0.17 A$ | 0.08 | 0.8 | | S |
| Dynamic | Characteristics | | | | | |
| C _{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ | | 73 | | pF |
| Coss | Output Capacitance | f = 1.0 MHz | | 7 | | pF |
| C _{rss} | Reverse Transfer Capacitance |] | | 3.4 | | pF |
| R_{G} | Gate Resistance | V _{GS} = 15 mV, f = 1.0 MHz | | 2.2 | | Ω |
| Switchin | g Characteristics (Note 2) | | | | | |
| t _{d(on)} | Turn-On Delay Time | $V_{DD} = 30 \text{ V}, \qquad I_D = 0.28 \text{ A},$ | | 1.7 | 3.4 | ns |
| t _r | Turn-On Rise Time | $V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$ | | 9 | 18 | ns |
| t _{d(off)} | Turn-Off Delay Time | 1 | | 17 | 31 | ns |
| t _f | Turn-Off Fall Time | 1 | | 2.4 | 5 | ns |
| Qg | Total Gate Charge | $V_{DS} = 30 \text{ V}, \qquad I_{D} = 0.22 \text{ A},$ | | 1.8 | 2.5 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10 V | | 0.2 | | nC |
| Q _{gd} | Gate-Drain Charge |] | | 0.3 | | nC |
| Drain-Sc | ource Diode Characteristics | and Maximum Ratings | , | • | | |
| I _S | Maximum Continuous Drain-Source | | | | 0.17 | Α |
| V _{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, \qquad I_{S} = 0.34 \text{ A(Note 2)}$ | | 0.8 | 1.3 | V |
| t _{rr} | Diode Reverse Recovery Time | $I_F = 0.17 \text{ A},$ | | 11 | | nS |
| Q _{rr} | Diode Reverse Recovery Charge | $d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$ | | 3 | | nC |

NOTE

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a) 350°C/W when mounted on a minimum pad..

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

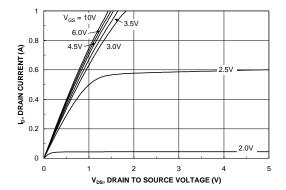


Figure 1. On-Region Characteristics.

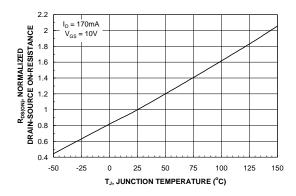


Figure 3. On-Resistance Variation with Temperature.

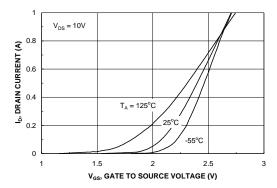


Figure 5. Transfer Characteristics.

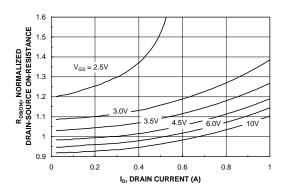


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

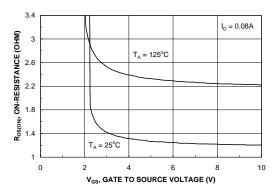


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

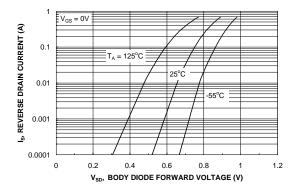
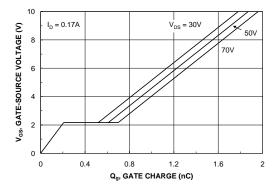


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



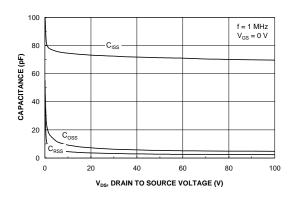


Figure 7. Gate Charge Characteristics.

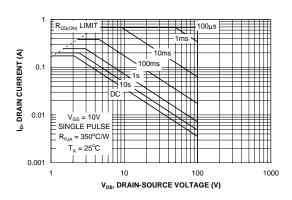


Figure 8. Capacitance Characteristics.

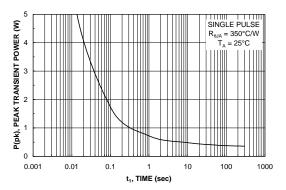


Figure 9. Maximum Safe Operating Area.



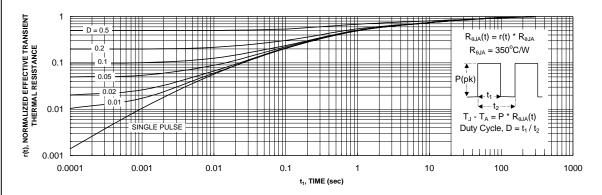


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1a. Transient thermal response will change depending on the circuit board design.

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